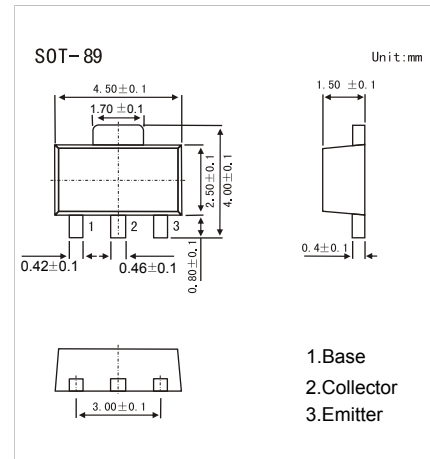


PNP Transistors

2SA1797

■ Features

- Low saturation voltage
- Excellent DC current gain characteristics
- Complements to 2SC4672



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-50	V
Collector - Emitter Voltage	V_{CE0}	-50	
Emitter - Base Voltage	V_{EB0}	-6	
Collector Current - Continuous	I_C	-2	A
Collector Current - Pulse	I_{CM}	-3	
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -50 \mu\text{A}, I_E = 0$	-50			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{mA}, I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -50 \mu\text{A}, I_C = 0$	-6			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -50 \text{V}, I_E = 0$			-100	nA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5 \text{V}, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{A}, I_B = -50 \text{mA}$			-0.35	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1 \text{A}, I_B = -50 \text{mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -2 \text{V}, I_C = -500 \text{mA}$	82		270	
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{V}, I_E = 0, f = 1 \text{MHz}$		36		pF
Transition frequency	f_T	$V_{CE} = -2 \text{V}, I_C = -500 \text{mA}, f = 100 \text{MHz}$		200		MHz

■ Classification of h_{FE}

Type	2SA1797-P	2SA1797-Q
Range	82-180	120-270
Marking	AGP	AGQ

PNP Transistors

2SA1797

■ Typical Characteristics

